

Silicon NPN Power Transistors

2SD2024

DESCRIPTION

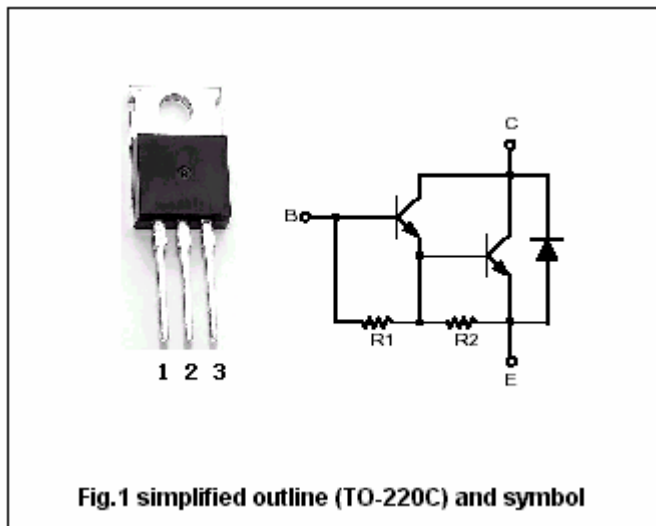
- With TO-220C package
- High DC current gain
- Low saturation voltage
- DARLINGTON

APPLICATIONS

- For low frequency power amplifier and power driver applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector -emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		10	A
P _C	Collector power dissipation	T _a =25	2	W
		T _C =25	40	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA; I _B =0	100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =50 μ A; I _E =0	100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A ; I _B =6mA			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			3.0	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =3V	1000		20000	

固电半导体

INCHANGE SEMICONDUCTOR

